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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	29
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	36-UFBGA, WLCSP
Supplier Device Package	36-WLCSP (2.61x2.88)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l051t8y7dtr

2.1 Device overview

Table 2. Ultra-low-power STM32L051x6/x8 device features and peripheral counts

Peripheral		STM32 L051K6	STM32L 051T6	STM32 L051C6	STM32 L051R6	STM32 L051K8	STM32L 051T8	STM32 L051C8	STM32 L051R8
Flash (Kbytes)		32				64			
Data EEPROM (Kbytes)		2				2			
RAM (Kbytes)		8				8			
Timers	General-purpose	3				3			
	Basic	1				1			
	LPTIMER	1				1			
RTC/SYSTICK/IWDG/ WWDG		1/1/1/1				1/1/1/1			
Communi- cation interfaces	SPI/I2S	3(2) ⁽¹⁾ /0	3(2) ⁽¹⁾ /0	4(2) ⁽¹⁾ /1	4(2) ⁽¹⁾ /1	3(2) ⁽¹⁾ /0	3(2) ⁽¹⁾ /0	4(2) ⁽¹⁾ /1	4(2) ⁽¹⁾ /1
	I ² C	1	2	2	2	1	2	2	2
	USART	2				2			
	LPUART	0	1	1	1	0	1	1	1
GPIOs		27 ⁽²⁾	29	37	51 ⁽³⁾	27 ⁽²⁾	29	37	51 ⁽³⁾
Clocks: HSE/LSE/HSI/MSI/LSI		0/1/1/1/1	0/1/1/1/1	1/1/1/1/1	1/1/1/1/1	0/1/1/1/1	0/1/1/1/1	1/1/1/1/1	1/1/1/1/1
12-bit synchronized ADC Number of channels		1 10	1 10	1 10	1 16 ⁽³⁾	1 10	1 10	1 10	1 16 ⁽³⁾
Comparators		2				2			
Max. CPU frequency		32 MHz							
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option							
Operating temperatures		Ambient temperature: –40 to +125 °C Junction temperature: –40 to +130 °C							
Packages		LQFP32, UFQFPN 32	WLCSP 36	LQFP48	LQFP64 TFBGA 64	LQFP32, UFQFPN 32	WLCSP 36	LQFP48	LQFP64 TFBGA 64

1. 2 SPI interfaces are USARTs operating in SPI master mode.

2. LQFP32 has two GPIOs, less than UFQFPN32 (27).

3. TFBGA64 has one GPIO, one ADC input and one capacitive sensing channel less than LQFP64.

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to ARM® Cortex®-M4, including ARM® Cortex®-M3 and ARM® Cortex®-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 ultra-low-power series are the best solution for applications such as gaz/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.

Table 6. STM32L0xx peripherals interconnect matrix (continued)

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop
RTC	TIM21	Timer triggered by Auto wake-up	Y	Y	Y	Y	-
	LPTIM	Timer triggered by RTC event	Y	Y	Y	Y	Y
All clock source	TIMx	Clock source used as input channel for RC measurement and trimming	Y	Y	Y	Y	-
GPIO	TIMx	Timer input channel and trigger	Y	Y	Y	Y	-
	LPTIM	Timer input channel and trigger	Y	Y	Y	Y	Y
	ADC	Conversion trigger	Y	Y	Y	Y	-

3.3 ARM[®] Cortex[®]-M0+ core with MPU

The Cortex-M0+ processor is an entry-level 32-bit ARM Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture that is easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area and power optimized 32-bit processor core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to its embedded ARM core, the STM32L051x6/8 are compatible with all ARM tools and software.

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L051x6/8 embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.4 Reset and supply management

3.4.1 Power supply schemes

- $V_{DD} = 1.65$ to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA} , $V_{DDA} = 1.65$ to 3.6 V: external analog power supplies for ADC reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.

3.4.2 Power supply supervisor

The devices have an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

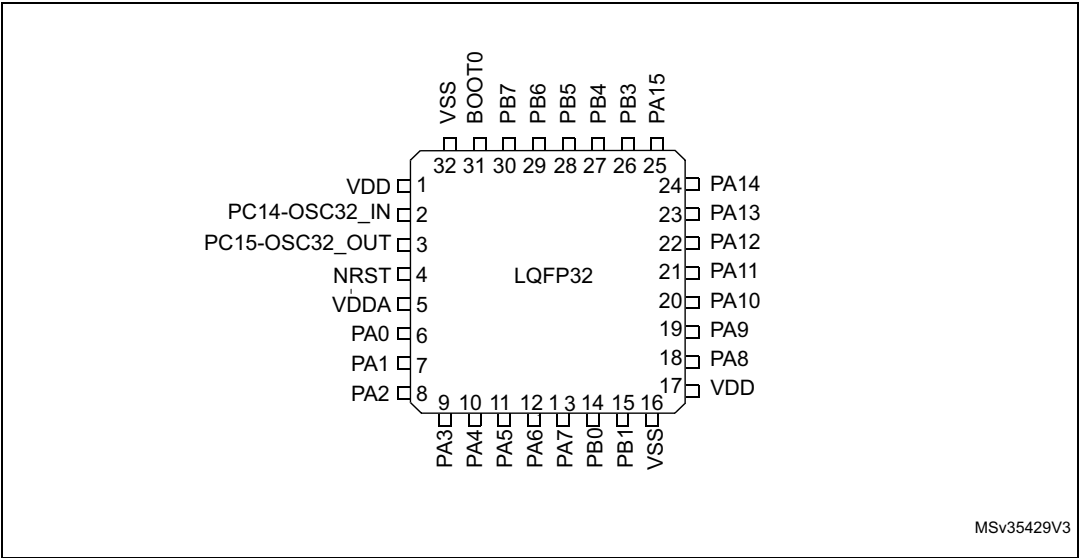
- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V_{DD} threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the V_{DD} min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

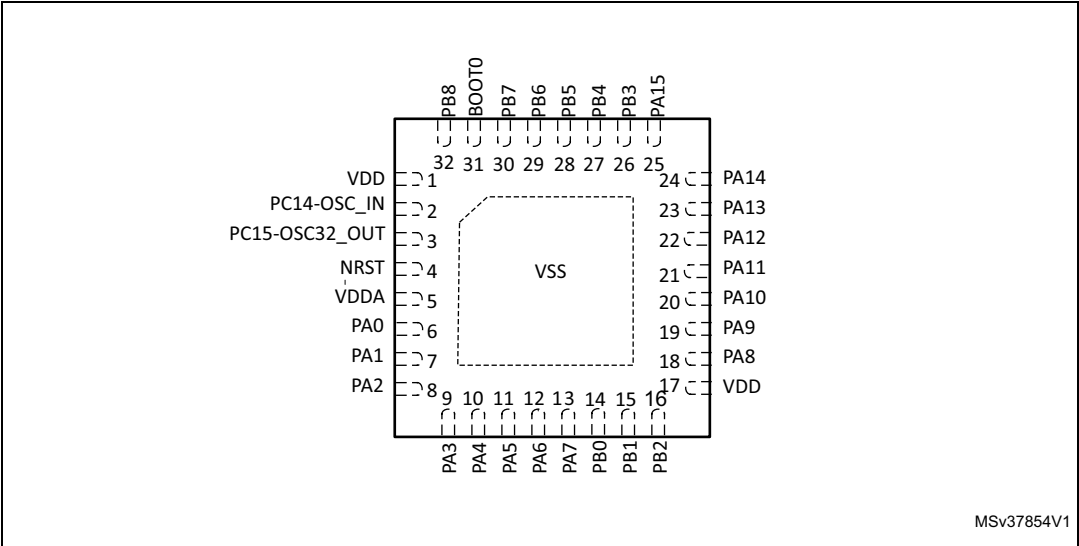
Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the

Figure 7. STM32L051x6/8 LQFP32 pinout



1. The above figure shows the package top view.

Figure 8. STM32L051x6/8 UFQFPN32 pinout



1. The above figure shows the package top view.

Table 18. Alternate function port C

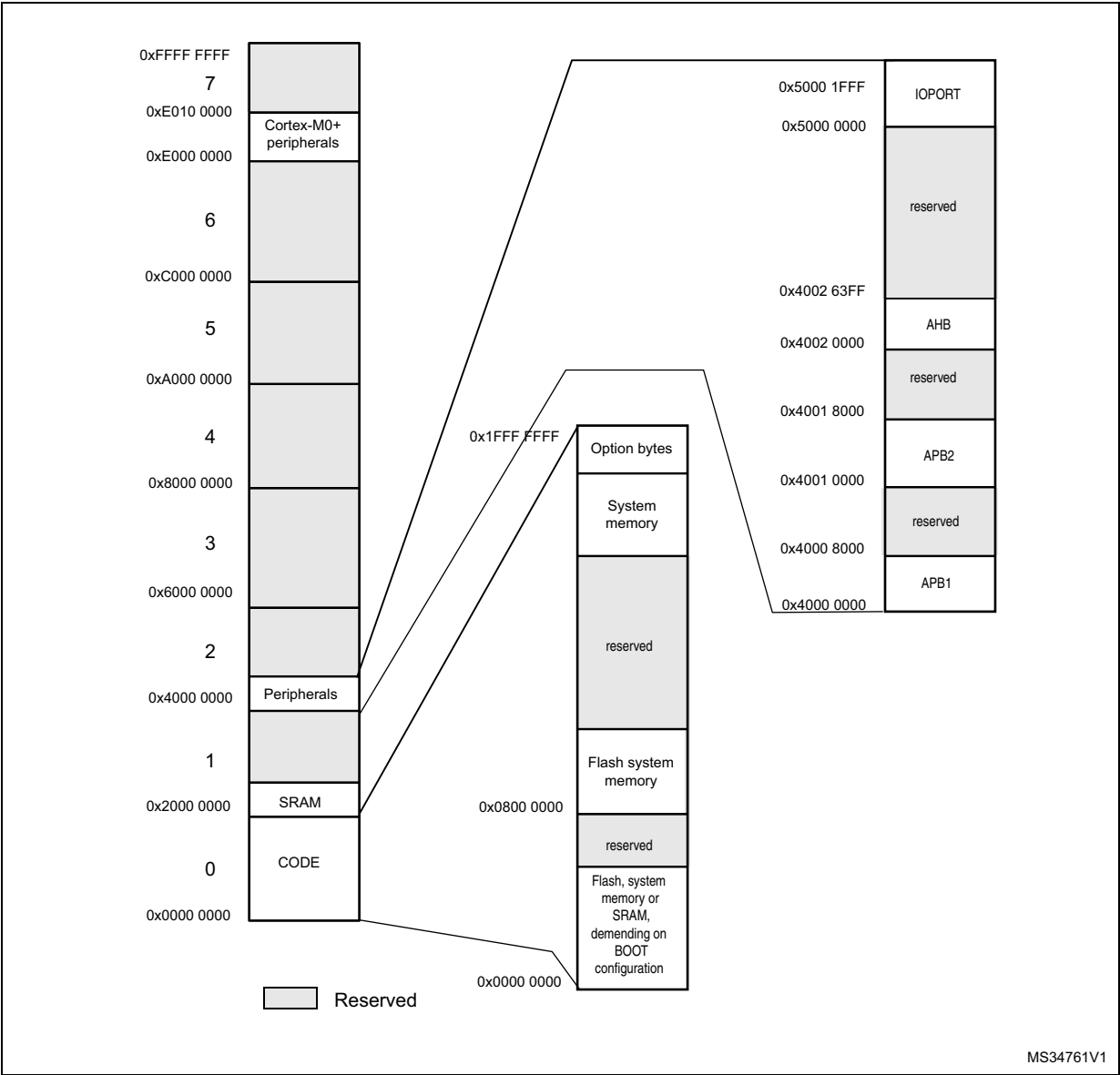
Port		AF0	AF1	AF2
		LPUART1/LPTIM/TIM21/12/EVENTOUT	-	SPI2/I2S2/LPUART1/EVENTOUT
Port C	PC0	LPTIM1_IN1	-	EVENTOUT
	PC1	LPTIM1_OUT	-	EVENTOUT
	PC2	LPTIM1_IN2	-	SPI2_MISO/I2S2_MCK
	PC3	LPTIM1_ETR	-	SPI2_MOSI/I2S2_SD
	PC4	EVENTOUT	-	LPUART1_TX
	PC5		-	LPUART1_RX
	PC6	TIM22_CH1	-	-
	PC7	TIM22_CH2	-	-
	PC8	TIM22_ETR	-	-
	PC9	TIM21_ETR	-	-
	PC10	LPUART1_TX	-	-
	PC11	LPUART1_RX	-	-
	PC12	-	-	-
	PC13	-	-	-
	PC14	-	-	-
	PC15	-	-	-

Table 19. Alternate function port D

Port		AF0	AF1
		LPUART1	-
Port D	PD2	LPUART1_RTS_DE	-

5 Memory mapping

Figure 9. Memory map



MS34761V1

Table 26. Embedded internal reference voltage⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{LPBUF}^{(4)}$	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
$V_{REFINT_DIV1}^{(4)}$	1/4 reference voltage	-	24	25	26	% V_{REFINT}
$V_{REFINT_DIV2}^{(4)}$	1/2 reference voltage	-	49	50	51	
$V_{REFINT_DIV3}^{(4)}$	3/4 reference voltage	-	74	75	76	

1. Refer to [Table 38: Peripheral current consumption in Stop and Standby mode](#) for the value of the internal reference current consumption (I_{REFINT}).
2. Guaranteed by test in production.
3. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
4. Guaranteed by design.
5. Shortest sampling time can be determined in the application by multiple iterations.
6. To guarantee less than 1% VREF_OUT deviation.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in [Figure 13: Current consumption measurement scheme](#).

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code if not specified otherwise.

The current consumption values are derived from the tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 23: General operating conditions](#) unless otherwise specified.

The MCU is placed under the following conditions:

- All I/O pins are configured in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time and prefetch is adjusted depending on fHCLK frequency and voltage range to provide the best CPU performance unless otherwise specified.
- When the peripherals are enabled $f_{APB1} = f_{APB2} = f_{APB}$
- When PLL is ON, the PLL inputs are equal to HSI = 16 MHz (if internal clock is used) or HSE = 16 MHz (if HSE bypass mode is used)
- The HSE user clock applied to OSCI_IN input follows the characteristic specified in [Table 40: High-speed external user clock characteristics](#)
- For maximum current consumption $V_{DD} = V_{DDA} = 3.6$ V is applied to all supply pins
- For typical current consumption $V_{DD} = V_{DDA} = 3.0$ V is applied to all supply pins if not specified otherwise

The parameters given in [Table 47](#), [Table 23](#) and [Table 24](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 23](#).

Table 35. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾	Unit
I _{DD} (Standby)	Supply current in Standby mode	Independent watchdog and LSI enabled	T _A = - 40 to 25°C	1.3	1.7
			T _A = 55 °C	-	2.9
			T _A = 85 °C	-	3.3
			T _A = 105 °C	-	4.1
			T _A = 125 °C	-	8.5
		Independent watchdog and LSI OFF	T _A = - 40 to 25°C	0.29	0.6
			T _A = 55 °C	0.32	0.9
			T _A = 85 °C	0.5	2.3
			T _A = 105 °C	0.94	3
			T _A = 125 °C	2.6	7

1. Guaranteed by characterization results at 125 °C, unless otherwise specified

Table 36. Average current consumption during Wakeup

Symbol	parameter	System frequency	Current consumption during wakeup	Unit
I _{DD} (Wakeup from Stop)	Supply current during Wakeup from Stop mode	HSI	1	mA
		HSI/4	0,7	
		MSI clock = 4,2 MHz	0,7	
		MSI clock = 1,05 MHz	0,4	
		MSI clock = 65 KHz	0,1	
I _{DD} (Reset)	Reset pin pulled down	-	0,21	
I _{DD} (Power-up)	BOR ON	-	0,23	
I _{DD} (Wakeup from StandBy)	With Fast wakeup set	MSI clock = 2,1 MHz	0,5	
	With Fast wakeup disabled	MSI clock = 2,1 MHz	0,12	

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked OFF
 - with only one peripheral clocked on

Table 37. Peripheral current consumption in Run or Sleep mode⁽¹⁾

Peripheral		Typical consumption, $V_{DD} = 3.0\text{ V}$, $T_A = 25\text{ °C}$				Unit
		Range 1, $V_{CORE}=1.8\text{ V}$ $VOS[1:0] = 01$	Range 2, $V_{CORE}=1.5\text{ V}$ $VOS[1:0] = 10$	Range 3, $V_{CORE}=1.2\text{ V}$ $VOS[1:0] = 11$	Low-power sleep and run	
APB1	I2C1	11	9.5	7.5	9	$\mu\text{A/MHz}$ (f_{HCLK})
	I2C2	4	3.5	3	2.5	
	LPTIM1	10	8.5	6.5	8	
	LPUART1	8	6.5	5.5	6	
	SPI2	9	4.5	3.5	4	
	USART2	14.5	12	9.5	11	
	TIM2	10.5	8.5	7	9	
	TIM6	3.5	3	2.5	2	
	WWDG	3	2	2	2	
APB2	ADC1 ⁽²⁾	5.5	5	3.5	4	$\mu\text{A/MHz}$ (f_{HCLK})
	SPI1	4	3	3	2.5	
	USART1	14.5	11.5	9.5	12	
	TIM21	7.5	6	5	5.5	
	TIM22	7	6	5	6	
	FIREWALL	1.5	1	1	0.5	
	DBGMCU	1.5	1	1	0.5	
	SYSCFG	2.5	2	2	1.5	
Cortex-M0+ core I/O port	GPIOA	3.5	3	2.5	2.5	$\mu\text{A/MHz}$ (f_{HCLK})
	GPIOB	3.5	2.5	2	2.5	
	GPIOC	8.5	6.5	5.5	7	
	GPIOD	1	0.5	0.5	0.5	
AHB	CRC	1.5	1	1	1	$\mu\text{A/MHz}$ (f_{HCLK})
	FLASH	0 ⁽³⁾	0 ⁽³⁾	0 ⁽³⁾	0 ⁽³⁾	
	DMA1	10	8	6.5	8.5	

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 43](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

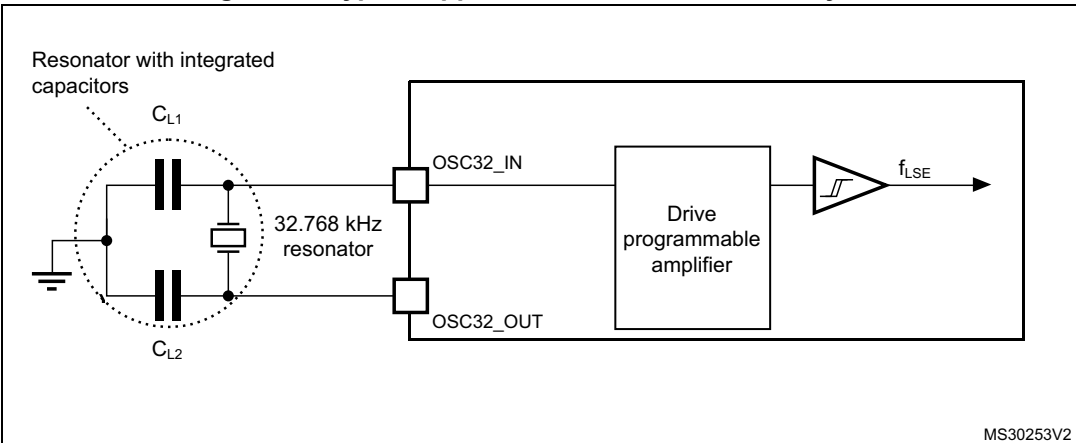
Table 43. LSE oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions ⁽²⁾	Min ⁽²⁾	Typ	Max	Unit
f_{LSE}	LSE oscillator frequency		-	32.768	-	kHz
G_m	Maximum critical crystal transconductance	LSEDRV[1:0]=00 lower driving capability	-	-	0.5	$\mu A/V$
		LSEDRV[1:0]= 01 medium low driving capability	-	-	0.75	
		LSEDRV[1:0] = 10 medium high driving capability	-	-	1.7	
		LSEDRV[1:0]=11 higher driving capability	-	-	2.7	
$t_{SU(LSE)}$ ⁽³⁾	Startup time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. Guaranteed by characterization results. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer. To increase speed, address a lower-drive quartz with a high- driver mode.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 22. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.

6.3.7 Internal clock source characteristics

The parameters given in [Table 44](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 23](#).

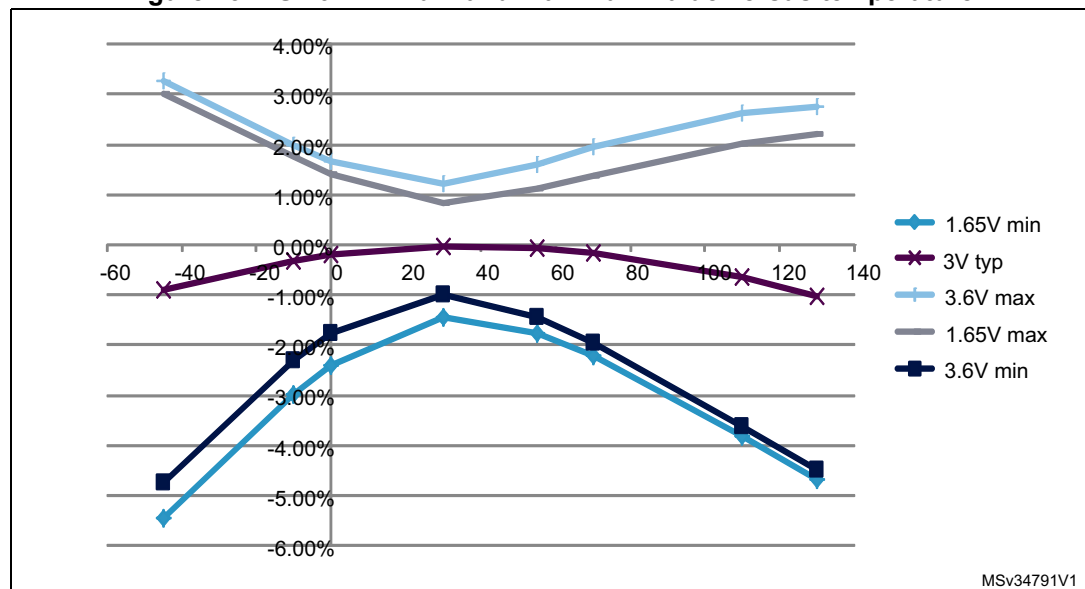
High-speed internal 16 MHz (HSI16) RC oscillator

Table 44. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	Frequency	$V_{DD} = 3.0\text{ V}$	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI16 user-trimmed resolution	Trimming code is not a multiple of 16	-	± 0.4	0.7	%
		Trimming code is a multiple of 16	-	-	± 1.5	%
$ACC_{HSI16}^{(2)}$	Accuracy of the factory-calibrated HSI16 oscillator	$V_{DDA} = 3.0\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$	-1 ⁽³⁾	-	1 ⁽³⁾	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = 0\text{ to }55\text{ }^{\circ}\text{C}$	-1.5	-	1.5	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = -10\text{ to }70\text{ }^{\circ}\text{C}$	-2	-	2	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = -10\text{ to }85\text{ }^{\circ}\text{C}$	-2.5	-	2	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = -10\text{ to }105\text{ }^{\circ}\text{C}$	-4	-	2	%
		$V_{DDA} = 1.65\text{ V to }3.6\text{ V}$ $T_A = -40\text{ to }125\text{ }^{\circ}\text{C}$	-5.45	-	3.25	%
$t_{SU(HSI16)}^{(2)}$	HSI16 oscillator startup time	-	-	3.7	6	μs
$I_{DD(HSI16)}^{(2)}$	HSI16 oscillator power consumption	-	-	100	140	μA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Figure 23. HSI16 minimum and maximum value versus temperature



SPI characteristics

Unless otherwise specified, the parameters given in the following tables are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 23](#).

Refer to [Section 6.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 70. SPI characteristics in voltage Range 1 ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	-	16	MHz
		Slave mode receiver			16	
		Slave mode Transmitter $1.71 < V_{DD} < 3.6V$	-	-	12 ⁽²⁾	
		Slave mode Transmitter $2.7 < V_{DD} < 3.6V$	-	-	16 ⁽²⁾	
$Duty_{(SCK)}$	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4 \cdot T_{pclk}$	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2 \cdot T_{pclk}$	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	$T_{pclk} - 2$	T_{pclk}	$T_{pclk} + 2$	
$t_{su(MI)}$	Data input setup time	Master mode	0	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	7	-	-	
$t_{h(SI)}$		Slave mode	3.5	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	15	-	36	
$t_{dis(SO)}$	Data output disable time	Slave mode	10	-	30	
$t_{v(SO)}$	Data output valid time	Slave mode $1.65 V < V_{DD} < 3.6 V$	-	18	41	
		Slave mode $2.7 V < V_{DD} < 3.6 V$	-	18	25	
		Master mode	-	4	7	
$t_{h(SO)}$	Data output hold time	Slave mode	10	-	-	
$t_{h(MO)}$		Master mode	0	-	-	

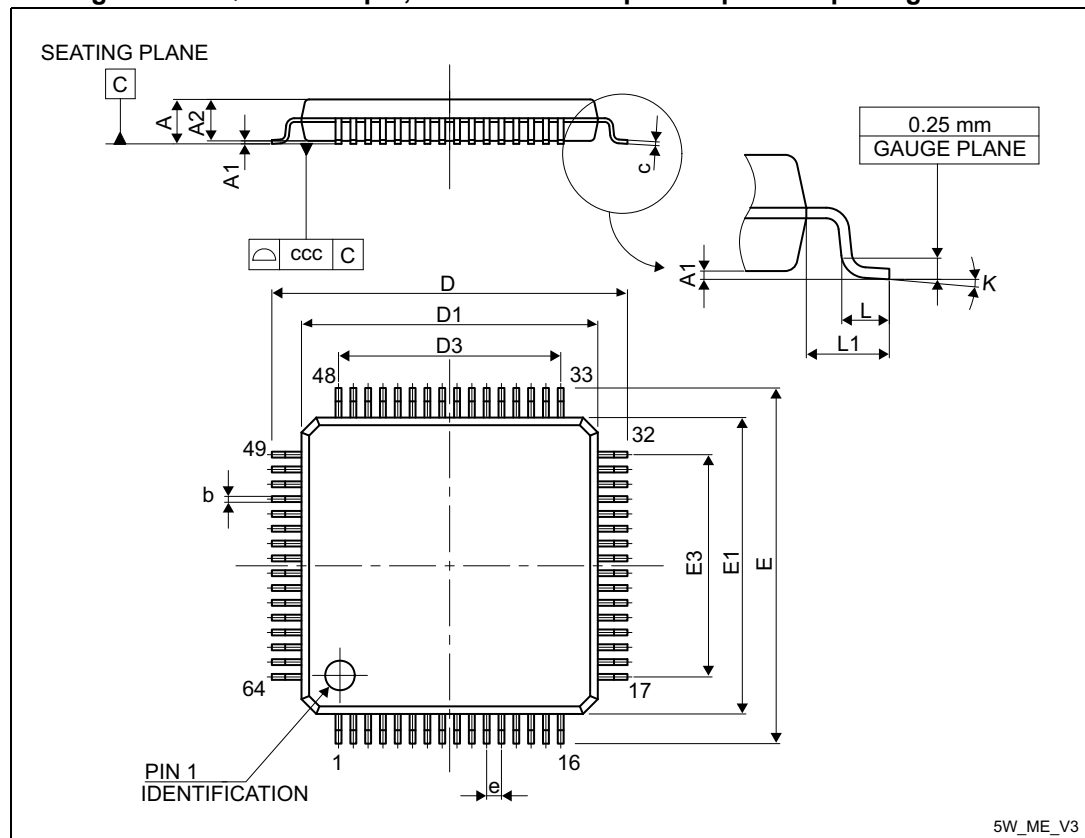
1. Guaranteed by characterization results.
2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while $Duty_{(SCK)} = 50\%$.

7 Package information

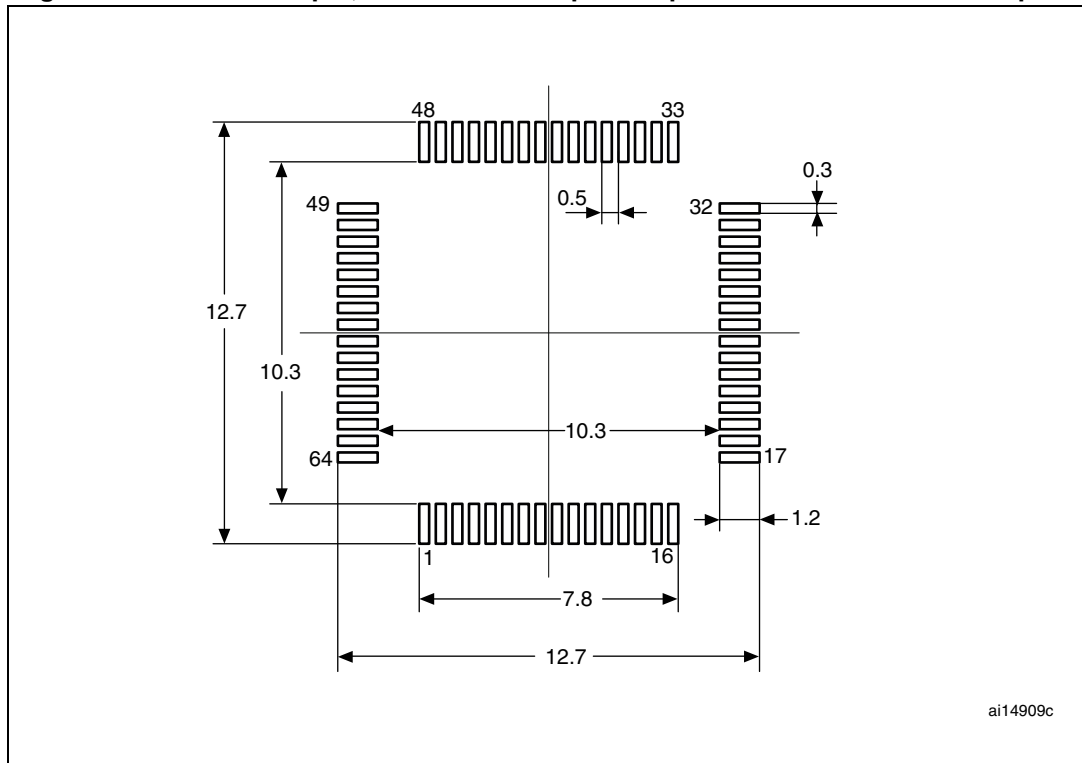
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status *are available at* www.st.com. ECOPACK® is an ST trademark.

7.1 LQFP64 package information

Figure 37. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline



1. Drawing is not to scale.

Figure 38. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint

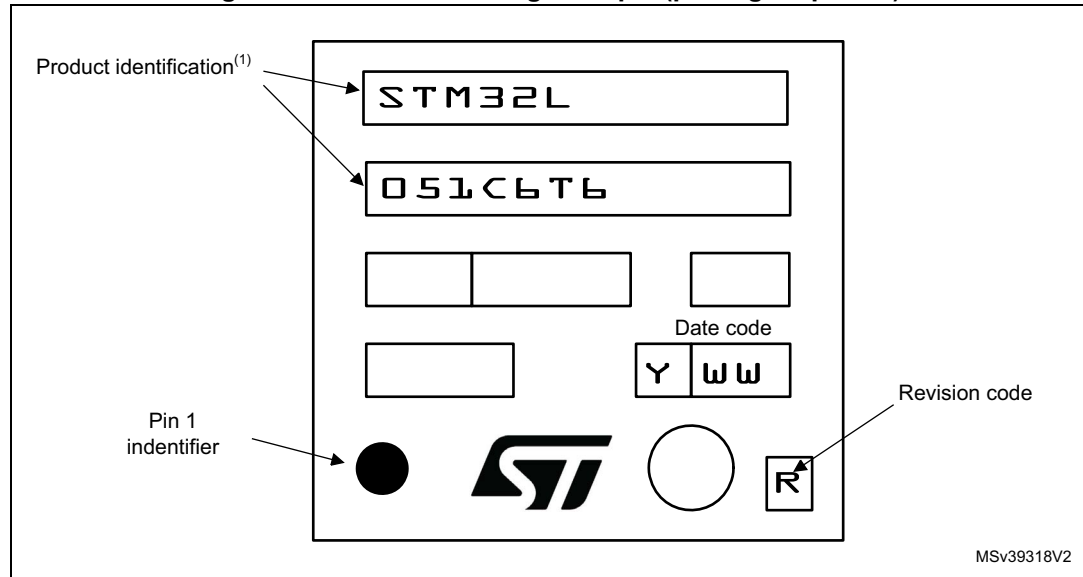
1. Dimensions are expressed in millimeters.

Device marking for LQFP48

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 45. LQFP48 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.4 Standard WLCSP36 package information

Figure 46. Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale package outline

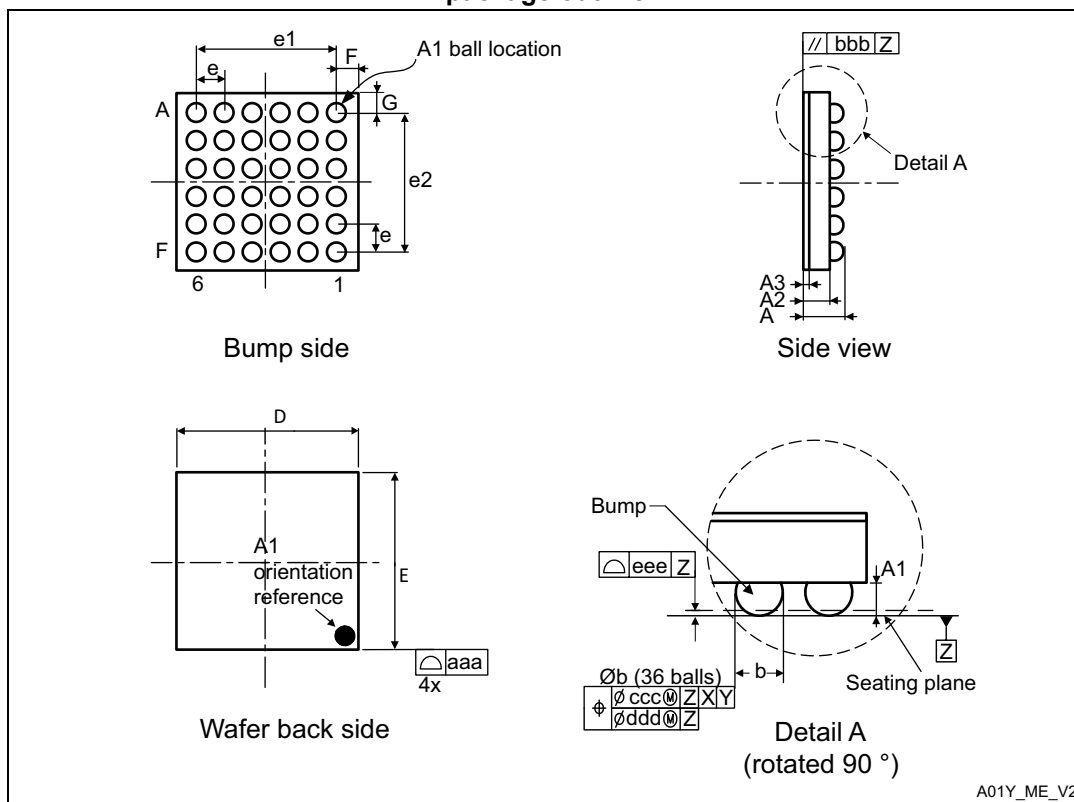
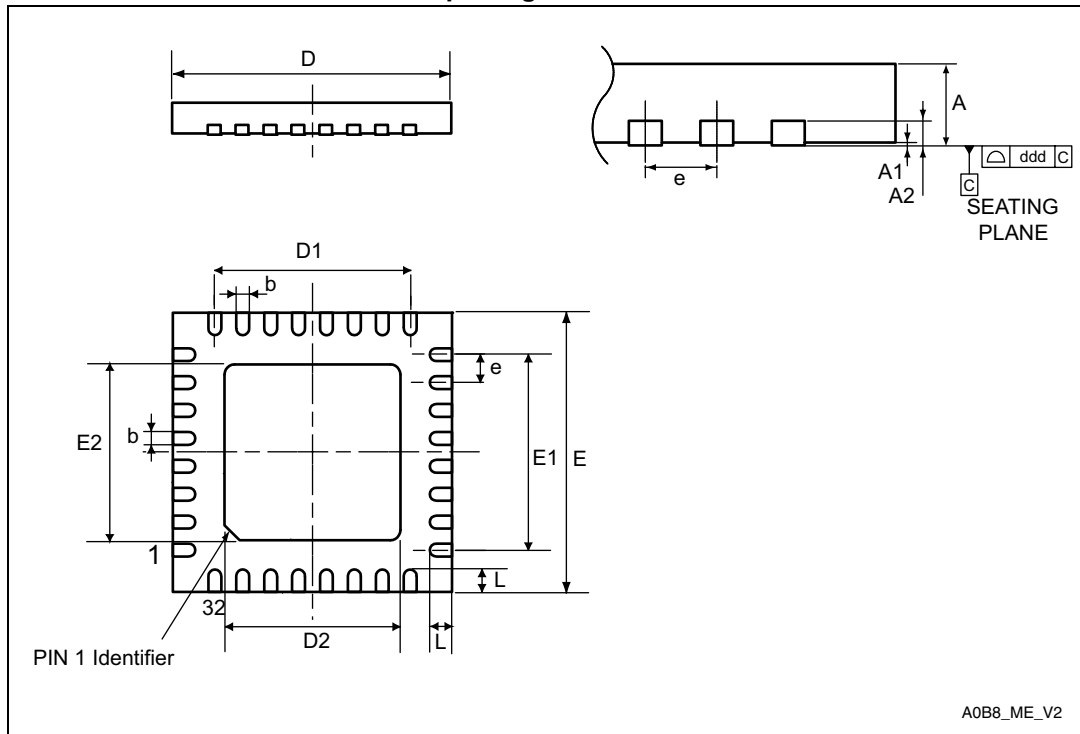


Table 78. Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	0.59	-	-	0.023
A1	-	0.18	-	-	0.007	-
A2	-	0.38	-	-	0.015	-
A3	-	0.025 ⁽²⁾	-	-	0.001	-
b	0.22	0.25	0.28	0.009	0.010	0.011
D	2.59	2.61	2.63	0.102	0.103	0.104
E	2.86	2.88	2.90	0.112	0.113	0.114
e	-	0.40	-	-	0.016	-
e1	-	2.00	-	-	0.079	-
e2	-	2.00	-	-	0.079	-

7.7 UFQFPN32 package information

Figure 54. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package outline



1. Drawing is not to scale.

8 Part numbering

Table 85. STM32L051x6/8 ordering information scheme

Example:	STM32	L	051	R	8	T	6	D	TR									
Device family																		
STM32 = ARM-based 32-bit microcontroller																		
Product type																		
L = Low power																		
Device subfamily																		
051 = Access line																		
Pin count																		
K = 32 pins																		
T = 36 pins																		
C = 48/49 pins																		
R = 64 pins																		
Flash memory size																		
6 = 32 Kbytes																		
8 = 64 Kbytes																		
Package																		
T = LQFP																		
H = TFBGA																		
U = UFQFPN																		
Y = Standard WLCSP pins																		
F = Thin WLCSP pins																		
Temperature range																		
6 = Industrial temperature range, −40 to 85 °C																		
7 = Industrial temperature range, −40 to 105 °C																		
3 = Industrial temperature range, −40 to 125 °C																		
Options																		
No character = V _{DD} range: 1.8 to 3.6 V and BOR enabled																		
D = V _{DD} range: 1.65 to 3.6 V and BOR disabled																		
Packing																		
TR = tape and reel																		
No character = tray or tube																		

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

9 Revision history

Table 86. Document revision history

Date	Revision	Changes
13-Feb-2014	1	Initial release.
29-Apr-2014	2	<p>Added WLCSP36 package. Updated Table 2: Ultra-low-power STM32L051x6/x8 device features and peripheral counts</p> <p>Updated Table 5: Functionalities depending on the working mode (from Run/active down to standby). Added Section 3.2: Interconnect matrix.</p> <p>Updated Figure 4: STM32L051x6/8 TFBGA64 ballout - 5x 5 mm</p> <p>Replaced TTa I/O structure by TC, updated PA0/4/5, PC5/14, BOOT0 and NRST I/O structure in Table 15: STM32L051x6/8 pin definitions.</p> <p>Updated Table 23: General operating conditions, Table 20: Voltage characteristics and Table 21: Current characteristics.</p> <p>Modified conditions in Table 26: Embedded internal reference voltage.</p> <p>Updated Table 27: Current consumption in Run mode, code with data processing running from Flash, Table 29: Current consumption in Run mode, code with data processing running from RAM, Table 31: Current consumption in Sleep mode, Table 32: Current consumption in Low-power run mode, Table 33: Current consumption in Low-power sleep mode, Table 34: Typical and maximum current consumptions in Stop mode and Table 35: Typical and maximum current consumptions in Standby mode. Added Figure 14: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS, Figure 15: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS, Figure 16: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 17: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 18: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF.</p> <p>Updated Table 42: HSE oscillator characteristics and Table 43: LSE oscillator characteristics. Added Figure 23: HSI16 minimum and maximum value versus temperature.</p> <p>Updated Table 53: ESD absolute maximum ratings, Table 55: I/O current injection susceptibility and Table 56: I/O static characteristics, and added Figure 24: VIH/VIL versus VDD (CMOS I/Os) and Figure 25: VIH/VIL versus VDD (TTL I/Os). Updated Table 57: Output voltage characteristics, Table 58: I/O AC characteristics and Figure 26: I/O AC characteristics definition.</p> <p>Updated Table 60: ADC characteristics, Table 62: ADC accuracy, and Figure 29: Typical connection diagram using the ADC. Updated Table 64: Temperature sensor characteristics.</p> <p>Updated Table 70: SPI characteristics in voltage Range 1 and Table 73: I2S characteristics.</p> <p>Added Figure 57: Thermal resistance.</p>